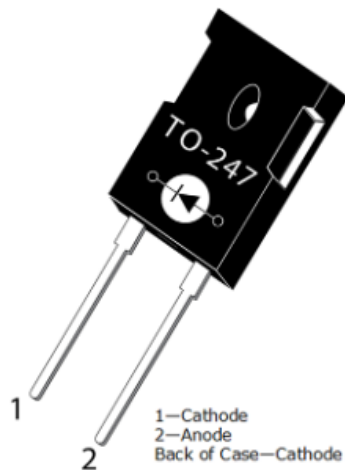


# MSC030SDA070B Zero Recovery Silicon Carbide Schottky Diode

## 1 Product Overview

This section shows the product overview for the MSC030SDA070B device.



### 1.1 Features

The following are key features of the MSC030SDA070B device:

- No reverse recovery/no forward recovery
- Low forward voltage
- Low leakage current
- Avalanche energy rated
- RoHS compliant

### 1.2 Benefits

The following are benefits of the MSC030SDA070B device:

- High switching frequency
- Low switching losses
- Low noise (EMI) switching
- Higher reliability systems
- Increased system power density

### 1.3 Applications

The MSC030SDA070B device is designed for the following applications:

- Power factor correction (PFC)
- Anti-parallel diode
  - Switch-mode power supply
  - Inverters/converters
  - Motor controllers
- Freewheeling diode
  - Switch-mode power supply
  - Inverters/converters
- Snubber/clamp diode

## 2 Device Specifications

This section details the device specifications for the MSC030SDA070B device.

### 2.1 Absolute Maximum Ratings

The following table shows the absolute maximum ratings for the MSC030SDA070B device. All ratings:  $T_c = 25\text{ }^\circ\text{C}$  unless otherwise specified.

**Table 1 • Absolute Maximum Ratings**

Symbol	Parameter		Ratings	Unit
$V_R$	Maximum DC reverse voltage		700	V
$V_{RRM}$	Maximum peak repetitive reverse voltage		700	
$V_{RWM}$	Maximum working peak reverse voltage		700	
$I_F$	Maximum DC forward current	$T_c = 25\text{ }^\circ\text{C}$	60	A
		$T_c = 135\text{ }^\circ\text{C}$	25	
		$T_c = 145\text{ }^\circ\text{C}$	21	
$I_{FRM}$	Repetitive peak forward surge current ( $T_c = 25\text{ }^\circ\text{C}$ , $t_p = 8.3\text{ ms}$ , half sine wave)		79	
$I_{FSM}$	Non-repetitive forward surge current ( $T_c = 25\text{ }^\circ\text{C}$ , $t_p = 8.3\text{ ms}$ , half sine wave)		146	
$P_{tot}$	Power dissipation	$T_c = 25\text{ }^\circ\text{C}$	188	W
		$T_c = 110\text{ }^\circ\text{C}$	81	
$T_J, T_{STG}$	Operating junction and storage temperature range		-55 to 175	$^\circ\text{C}$
$T_L$	Lead temperature for 10 seconds		300	
$E_{AS}$	Single pulse avalanche energy (starting $T_J = 25\text{ }^\circ\text{C}$ , $L = 0.22\text{ mH}$ , peak $I_L = 30\text{ A}$ )		100	mJ

The following table shows the thermal and mechanical characteristics of the MSC030SDA070B device.

**Table 2 • Thermal and Mechanical Characteristics**

Symbol	Characteristic/Test Conditions	Min	Typ	Max	Unit
$R_{\theta JC}$	Junction-to-case thermal resistance		0.56	0.80	$^\circ\text{C}/\text{W}$
$Wt$	Package weight		0.22		oz
			6.2		g
	Mounting torque, 6-32 or M3 screw			10	lbf-in
				1.1	N-m

## 2.2 Electrical Performance

The following table shows the static characteristics of the MSC030SDA070B device.

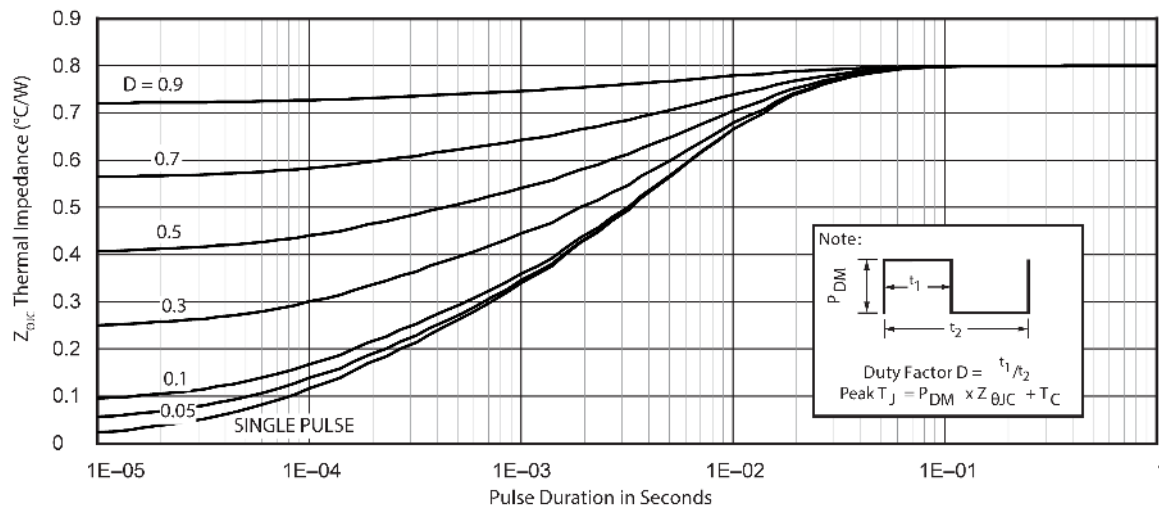
**Table 3 • Static Characteristics**

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
$V_F$	Forward voltage	$I_F = 30\text{ A}, T_J = 25\text{ }^\circ\text{C}$	1.5	1.8		V
		$I_F = 30\text{ A}, T_J = 175\text{ }^\circ\text{C}$		1.75		
$I_{RM}$	Reverse leakage current	$V_R = 700\text{ V}, T_J = 25\text{ }^\circ\text{C}$	1	200		$\mu\text{A}$
		$V_R = 700\text{ V}, T_J = 175\text{ }^\circ\text{C}$		10		
$Q_C$	Total capacitive charge	$V_R = 400\text{ V}, T_J = 25\text{ }^\circ\text{C}$		83		nC
$C_J$	Junction capacitance	$V_R = 1\text{ V}, T_J = 25\text{ }^\circ\text{C}, f = 1\text{ MHz}$		1200		pF
	Junction capacitance	$V_R = 200\text{ V}, T_J = 25\text{ }^\circ\text{C}, f = 1\text{ MHz}$		150		
	Junction capacitance	$V_R = 400\text{ V}, T_J = 25\text{ }^\circ\text{C}, f = 1\text{ MHz}$		128		

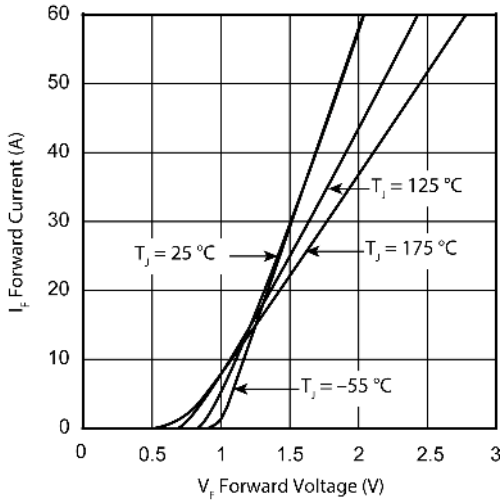
## 2.3 Performance Curves

This section shows the typical performance curves for the MSC030SDA070B device.

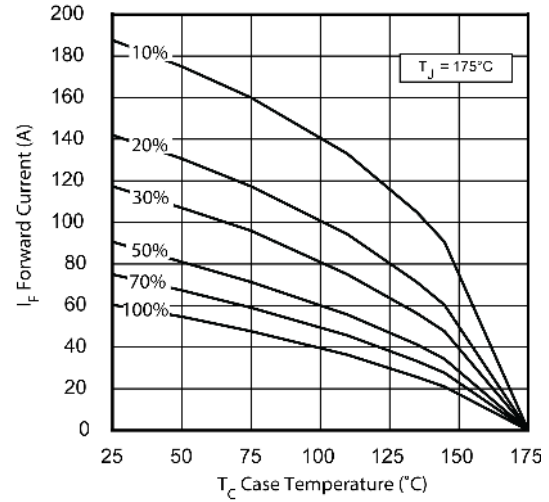
**Figure 1 • Maximum Transient Thermal Impedance**



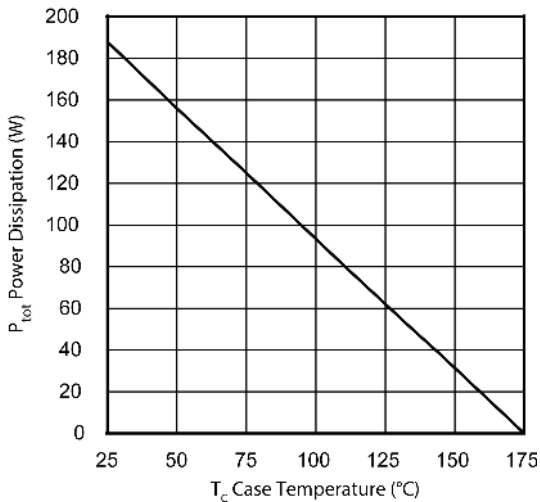
**Figure 2 • Forward Current vs. Forward Voltage**



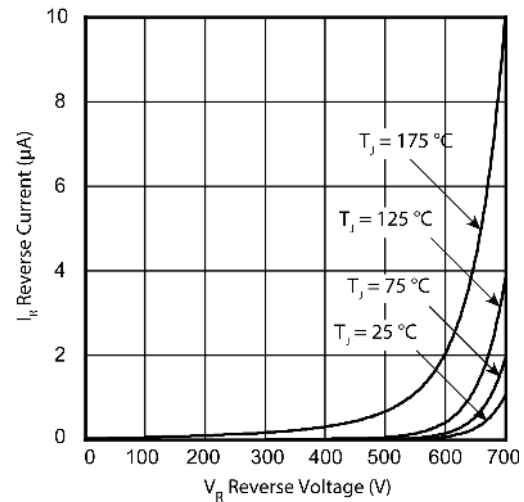
**Figure 3 • Max. Forward Current vs. Case Temp.**



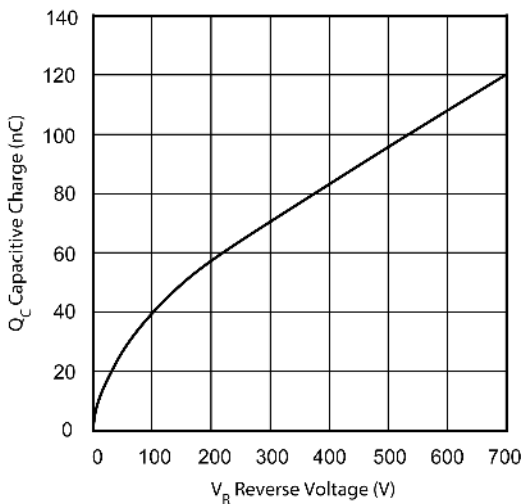
**Figure 4 • Max. Power Dissipation vs. Case Temp.**



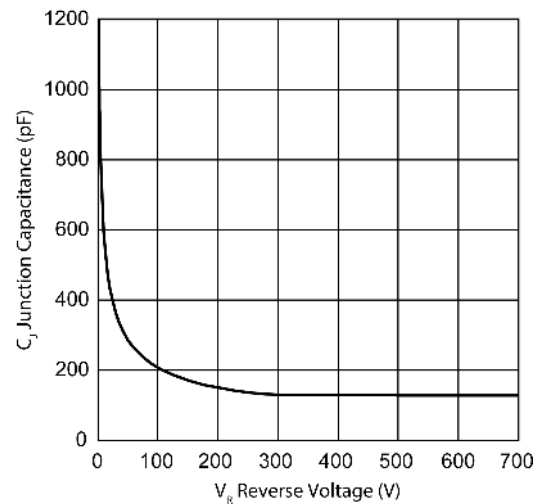
**Figure 5 • Reverse Current vs. Reverse Voltage**



**Figure 6 • Total Capacitive Charge vs. Reverse Voltage**



**Figure 7 • Junction Capacitance vs. Reverse Voltage**



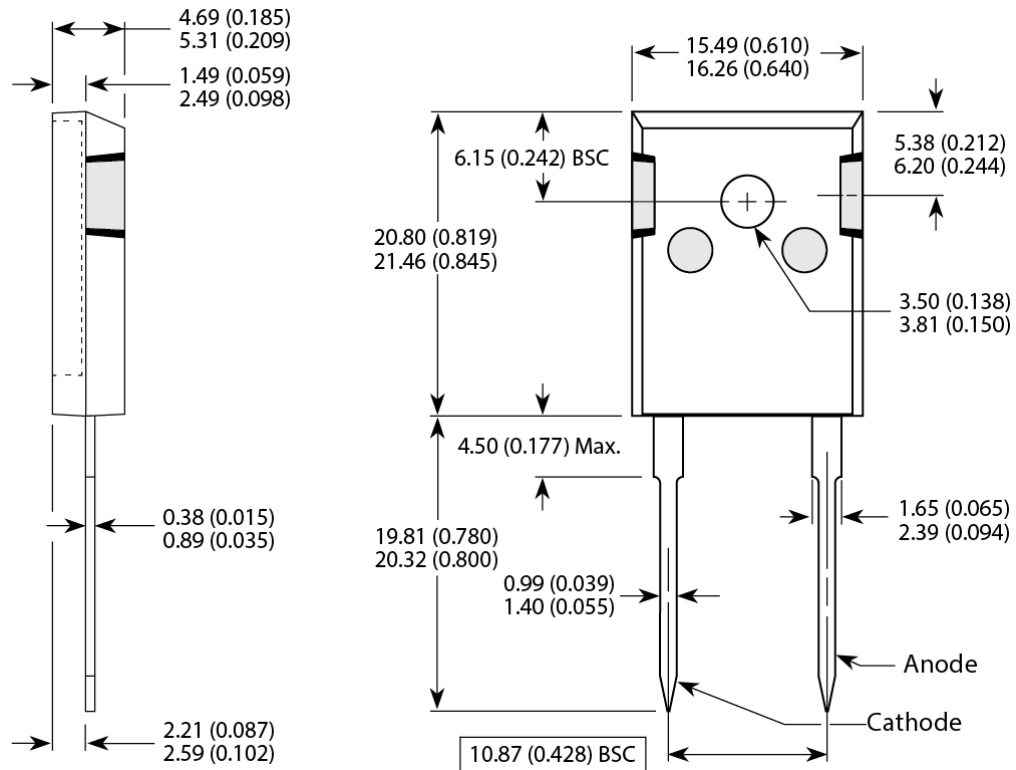
### 3 Package Specification

This section outlines the package specification for the MSC030SDA070B device.

#### 3.1 Package Outline Drawing

This section details the TO-247 package drawing of the MSC030SDA070B device. Dimensions are in millimeters and (inches).

Figure 8 • Package Outline Drawing





**Microsemi Headquarters**

One Enterprise, Aliso Viejo,  
CA 92656 USA

Within the USA: +1 (800) 713-4113

Outside the USA: +1 (949) 380-6100

Sales: +1 (949) 380-6136

Fax: +1 (949) 215-4996

Email: [sales.support@microsemi.com](mailto:sales.support@microsemi.com)

[www.microsemi.com](http://www.microsemi.com)

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